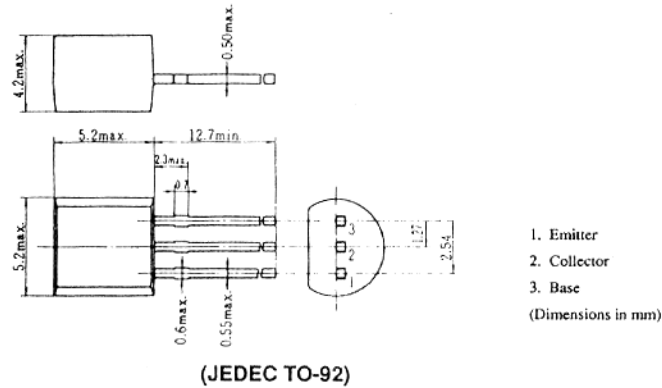


2SA893, 2SA893A

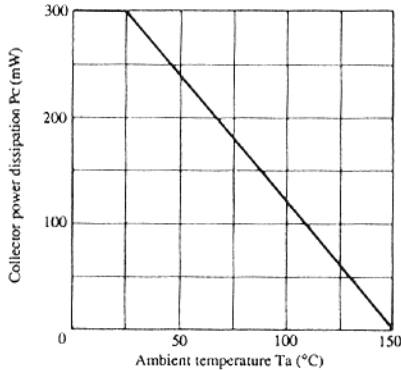
SILICON PNP EPITAXIAL
LOW FREQUENCY HIGH VOLTAGE AMPLIFIER
Complementary pair with 2SC1890/A



■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SA893	2SA893A	Unit
Collector to base voltage	V _{CBO}	-90	-120	V
Collector to emitter voltage	V _{CEO}	-90	-120	V
Emitter to base voltage	V _{EBO}	-5	-5	V
Collector current	I _C	-50	-50	mA
Collector power dissipation	P _C	300	300	mW
Junction temperature	T _J	150	150	°C
Storage temperature	T _{stg}	-55 to +150	-55 to +150	°C

MAXIMUM COLLECTOR DISSIPATION
CURVE



■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	2SA893			2SA893A			Unit
			min.	typ.	max.	min.	typ.	max.	
Collector to emitter break-down voltage	V _{(BR)CEO}	I _C = -1mA, R _{BE} = ∞	-90	—	—	-120	—	—	V
Collector cutoff current	I _{CBO}	V _{CB} = -75V, I _E = 0	—	—	-0.5	—	—	—	μA
		V _{CB} = -100V, I _E = 0	—	—	—	—	—	-0.5	
DC current transfer ratio	h _{FE} *	V _{CE} = -12V, I _C = -2mA	250	—	800	250	—	800	
Base to emitter voltage	V _{BE}	V _{CE} = -12V, I _C = -2mA	—	—	-0.75	—	—	-0.75	V
Collector to emitter saturation voltage	V _{CE(sat)}	I _C = -10mA, I _B = -1mA	—	—	-0.5	—	—	-0.5	V
Gain bandwidth product	f _T	V _{CE} = -12V, I _C = -2mA	—	120	—	—	120	—	MHz
Collector output capacitance	C _{ob}	V _{CB} = -25V, I _E = 0, f = 1MHz	—	1.8	—	—	1.8	—	pF
Noise figure	NF	V _{CE} = -6V, I _C = -50μA R _g = 50kΩ, f = 1kHz	—	2	10	—	2	10	dB

* The 2SA893/A is grouped by h_{FE} as follows.

D	E
250 to 500	400 to 800

■ See characteristic curves of 2SA872 and 2SA872A.